

Writing, reading and transporting spin in antiferromagnets



M. Kläui^{1,2}



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Johannes Gutenberg-Universität Mainz, Germany

²QuSpin, NTNU, Trondheim, Norway

- **Reading Antiferromagnetic systems:**
Imaging and electrical read-out of bulk, thin film and 2D antiferromagnets
- **Writing Antiferromagnetic systems:**
Field- and Strain-induced switching in AFMs
Bulk spin orbit torque-induced switching in AFMs
Interfacial spin orbit torque switching in AFMs
- **Long distance Spin Transport in antiferromagnets**

Writing, reading and transporting spin in antiferromagnets



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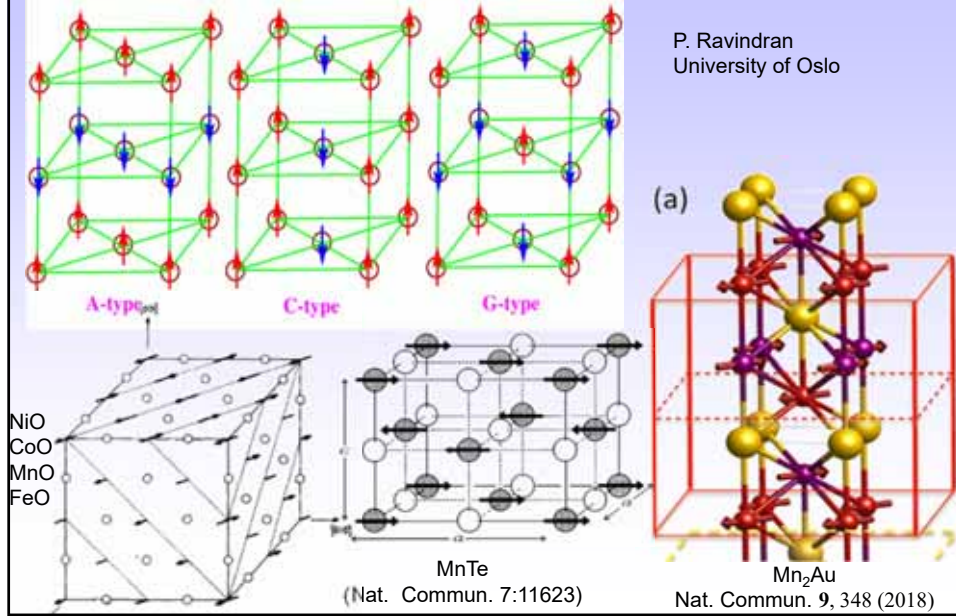


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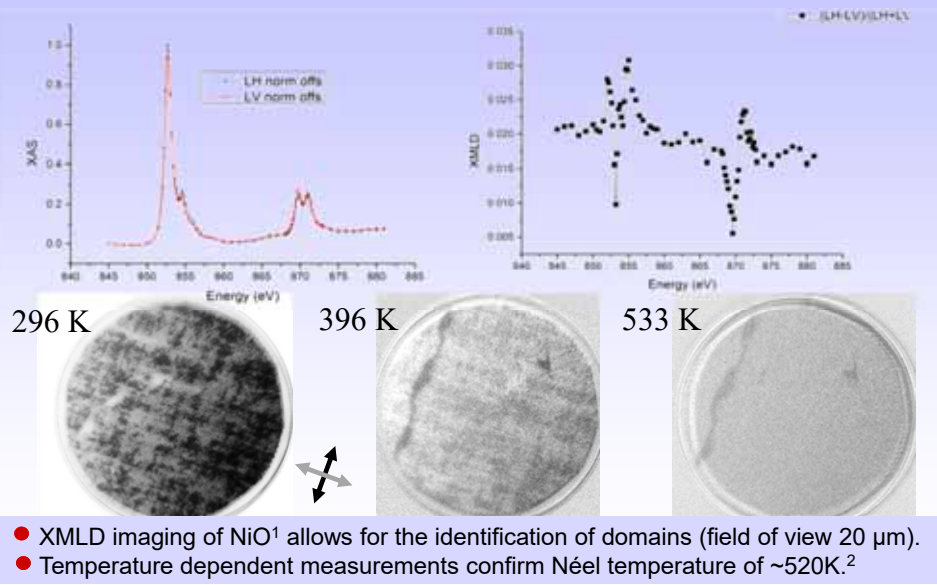
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1 Antiferromagnets

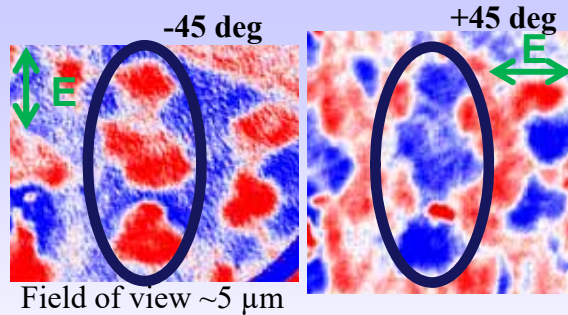


1. Reading Antiferromagnets (I) – XMLD of NiO



¹H. Ohldag, PhD Thesis; J. Stoehr et al., Phys. Rev. Lett. 83, 1862 (1999); ²L. Baldrati et al., PRB 98, 024422 (2018)

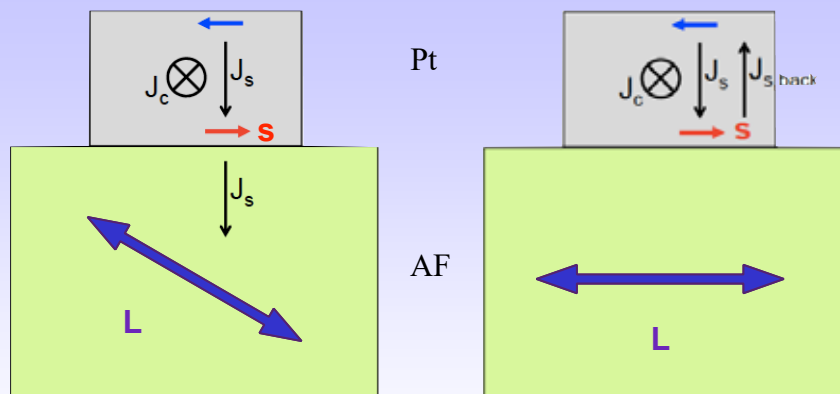
1. Reading Antiferromagnets (I) – XMLD of Mn₂Au



- Photoemission Electron Microscopy with linear dichroism contrast (XMLD-PEEM).
- Contrast is observed and by rotating the sample by 90° magnetic origin of μm sized domain signal can be confirmed.¹

¹A. Sapozhnik, M. Jourdan, M. Kläui et al., Phys. Rev. B **97**, 134429 (2018)

1. Reading Antiferromagnets electrically (II) - SMR



enhanced dissipation in Pt

reduced dissipation in Pt

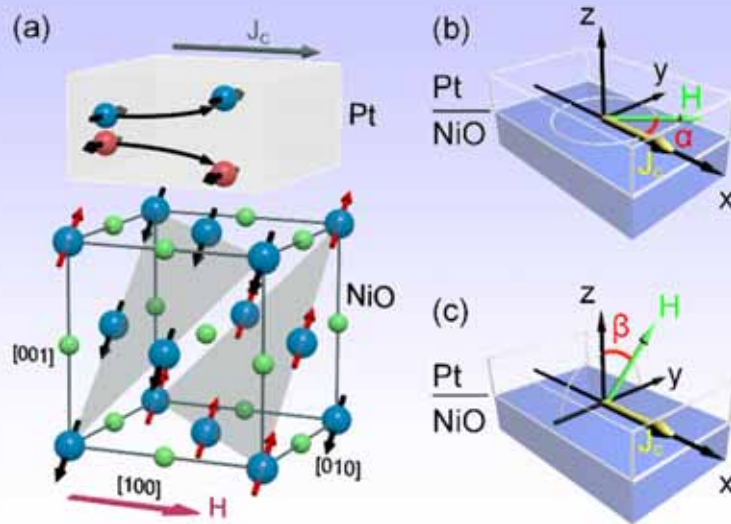
$$R = R_0 - \Delta R (Ls)^2$$

S. Gönnerwein

- Resistance is predicted to vary in a AFM/Pt bilayer for Néel vector parallel and perpendicular to current flow¹ → Spin Hall Magnetoresistance²

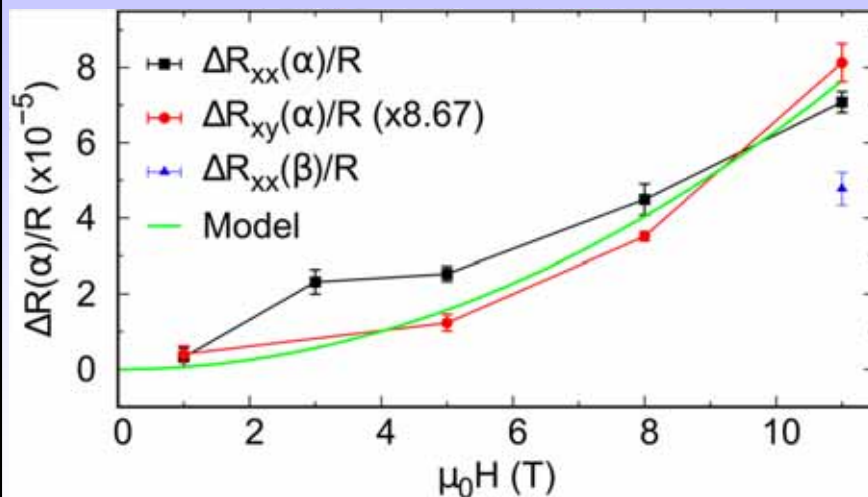
¹A. Manchon, Phys. Stat. Sol. – Rap. Res. Lett. **11**, 1600409 (2017); ²H. Nakayama et al., PRL **110**, 206601 (2013).

1. Reading Antiferromagnets by SMR (NiO)



¹ L. Baldrati, MK et al., Phys. Rev. B **98**, 024422 (2018); G. Hoozeboom et al., Appl. Phys. Lett. **111**, 052409 (2017)

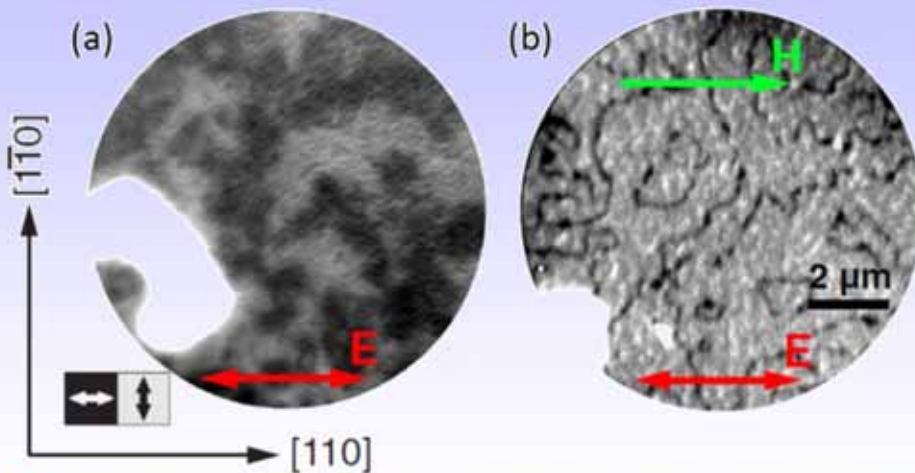
1. Reading Antiferromagnets by SMR (NiO)



- By rotating a strong field, the Néel vector is rotated (spin – flop) → negative SMR
- The SMR amplitude as a function of magnetic field shows the distribution of the magnetic fields needed to align the Néel vector in different domains.¹

¹ L. Baldrati, MK et al., Phys. Rev. B **98**, 024422 (2018); J. Fischer et al., Phys. Rev. B **97**, 014417 (2018)

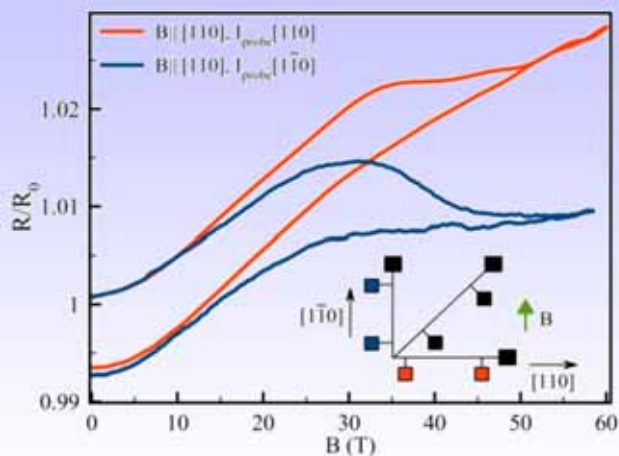
2. Reading Antiferromagnets – identifying AMR in Mn_2Au



- As grown, Mn_2Au comprises many domains with no net Néel vector orientation.
- When applying a field along one of the cubic easy axes above the spin-flop (50T): → orientation of Néel vector perpendicular to the field.

¹ S. Y. Bodnar, M. Jourdan, M. Kläui et al., arxiv:1909.12606 (2019)

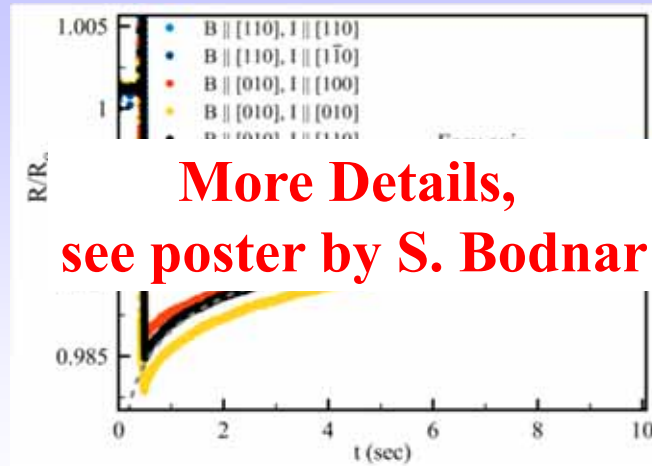
2. Reading Antiferromagnets – identifying AMR in Mn_2Au



- By applying a strong field, the Néel vector is rotated (> 30T)
- Between 0 field and 50 T → large change > 3%
- Remanent persistent difference much smaller: MR of ~0.1% → Origin?

¹ S. Y. Bodnar, M. Jourdan, M. Kläui et al., arxiv:1909.12606 (2019)

2. Reading Antiferromagnets – identifying AMR in Mn_2Au



**More Details,
see poster by S. Bodnar**

- Relaxation of the spin configuration on second timescales \rightarrow thermal activation
Current explanation: Remanent/persistent change is AMR of the domains: 0.1%
- MR during field application of 3% due to Domain Wall Magnetoresistance!

¹ S. Y. Bodnar, M. Jourdan, M. Kläui et al., arxiv:1909.12606 (2019)

2. Summary of Read-Out:

- 1. Electrical read-out:
 - Insulators: Spin Hall Magnetoresistance (SMR)
 - Metals:
 - Anisotropic magnetoresistance (domains)
 - Domain Wall magnetoresistances (DWs)
- 2. Imaging read-out:
 - Metals&Insulators: X-ray magnetic linear dichroism as contrast mechanism combined with x-ray microscopy (PEEM, STXM)

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Interfacial spin orbit torque switching in AFMs

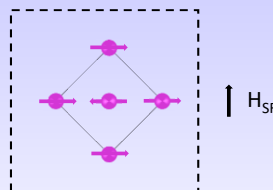
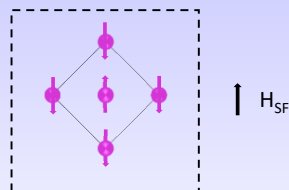
• Long distance Spin Transport in antiferromagnets

Mathias Kläui

SPICE Workshop, Mainz, 8.10.2019

3. Magnetic field-induced reorientation in Mn_2Au probed by XMLD

Two AFM domains with different orientation of moments



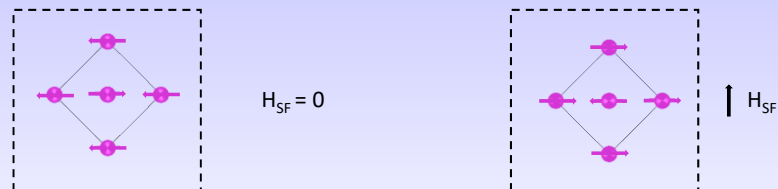
➤ Switching from one easy axis to the other upon applying a high magnetic field

➤ Moments preserve their initial orientation

- By applying a strong field, a spin-flop transition can be induced and the Néel vector aligns perpendicularly to the field direction

3. Magnetic field-induced reorientation in Mn_2Au probed by XMLD

Two AFM domains with different orientation of moments



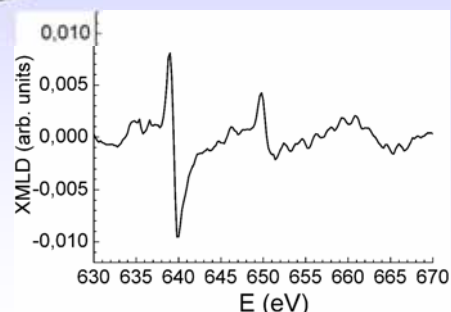
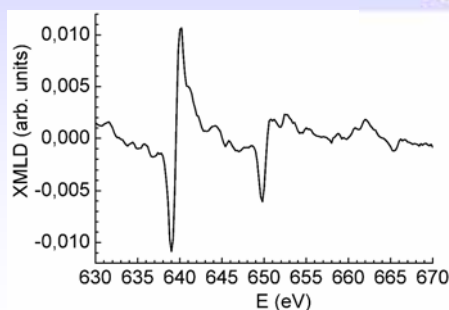
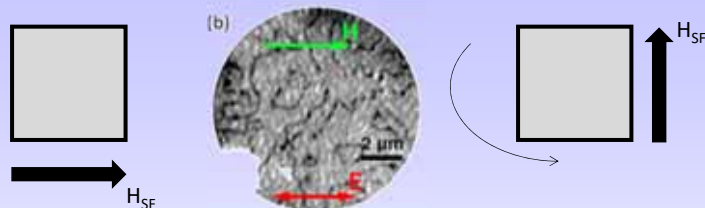
- Switching from one easy axis to the other upon applying a high magnetic field
- Moments preserve their initial orientation

However fast pulses can lead to Domain Wall motion in AFMs

H. Gomonay, MK et al., APL 109, 142404 (2016)

- By applying a strong field, a spin-flop transition can be induced and the Néel vector aligns perpendicularly to the field direction.
- For the Néel vector perpendicular to the field, only small transient canting occurs.

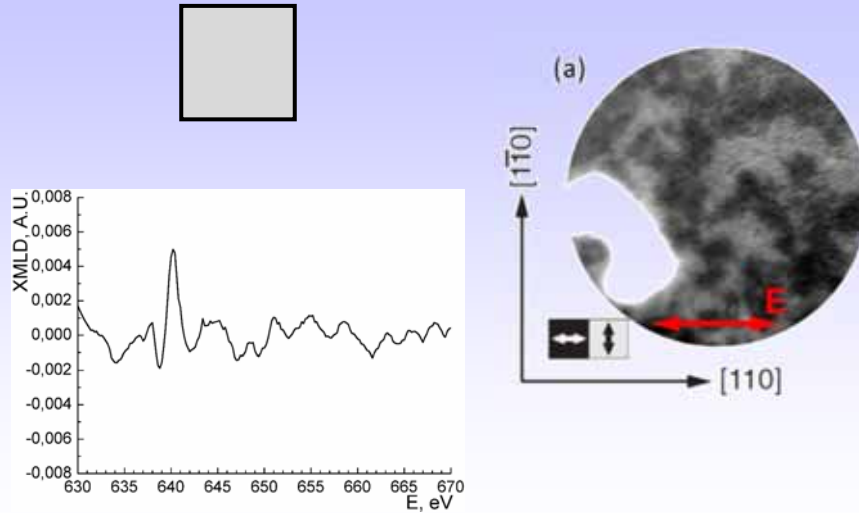
3. Magnetic field-induced reorientation in Mn_2Au probed by XMLD



- XMLD-imaging shows clear dichroism due to the alignment of the Néel vector.

A. Sapozhnik, M. Jourdan, MK et al., Phys. Status Solidi RRL **11**, 1600438 (2017).

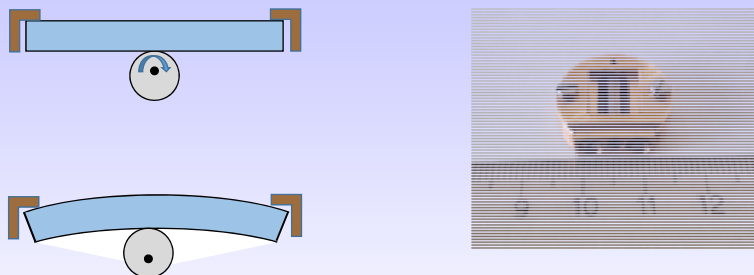
3. Magnetic field-induced reorientation in Mn_2Au probed by XMLD



- Reference sample – same structure not exposed to strong field shows no XMLD!

A. Sapozhnik, M. Jourdan, MK et al., Phys. Status Solidi RRL **11**, 1600438 (2017).

3. Strain-induced writing of Mn_2Au

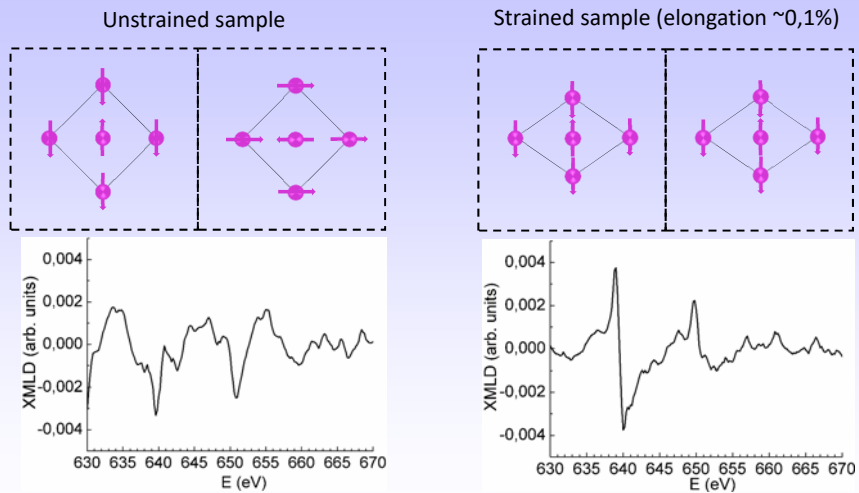


- Compatibility with UHV conditions
- Controllable value of strain
- Monitoring of strain with a strain gauge

- Expected strain-induced uniaxial anisotropy → apply strain to the sample!

A. Sapozhnik, M. Jourdan, MK et al., Phys. Status Solidi RRL **11**, 1600438 (2017).

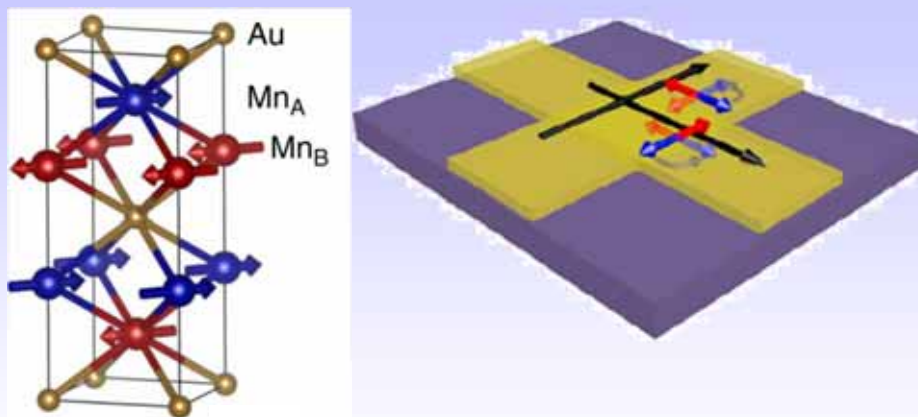
3. Engineering the spin structure of Mn_2Au by strain



- Application of strain (0,1%) leads to alignment of Néel vector visible from XMLD!
- Spin structure can be controlled by strain \rightarrow preparation of desired spin state!

A. Sapozhnik, M. Jourdan, MK et al., Phys. Status Solidi RRL **11**, 1600438 (2017).

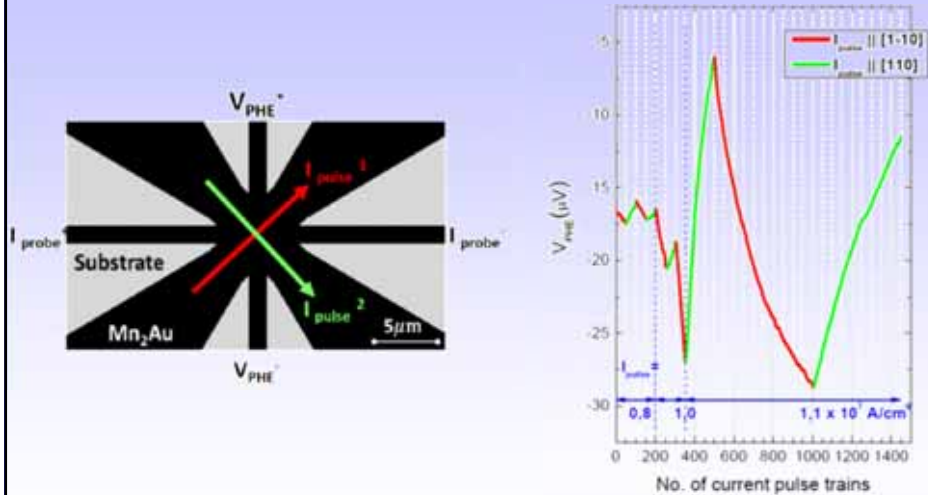
3. Spin-orbit torque switching of Mn_2Au



- Prediction of bulk spin orbit torques acting on the Néel order in AFM Mn_2Au ^{1,2,3} \rightarrow manipulation of magnetization using electric currents (first observed in CuMnAs ⁴).

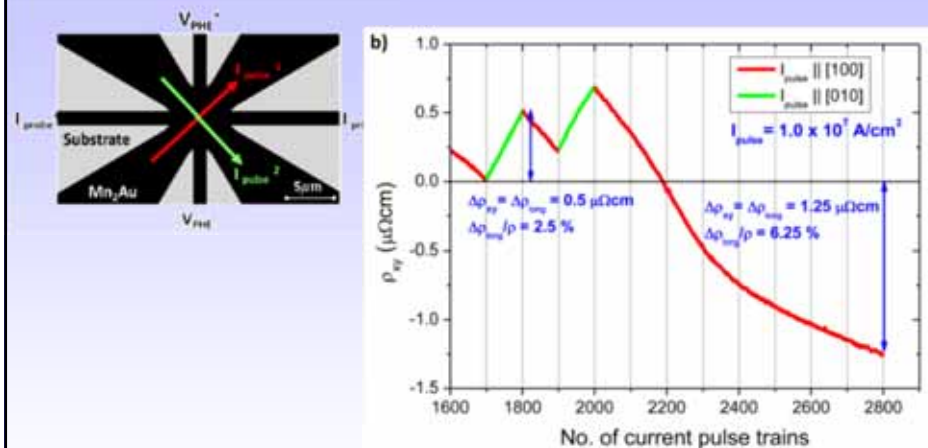
¹J. Zelezny, et al., PRL **113**, 157201 (2014); ²S. Bodnar, MK et al., Nature Comms. **9**, 348 (2018)

³M. Meinert et al., PR Applied **9**, 064040 (2018); ⁴P. Wadley et al., Science **351**, 587 (2016);

3. Bulk spin orbit torque switching in Mn_2Au 

- Bulk Néel spin orbit torques have been predicted to switch the Néel vector.
- Non-linear switching as a function of current density \rightarrow heating effects important!

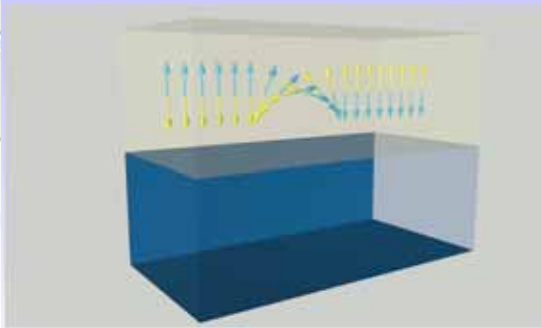
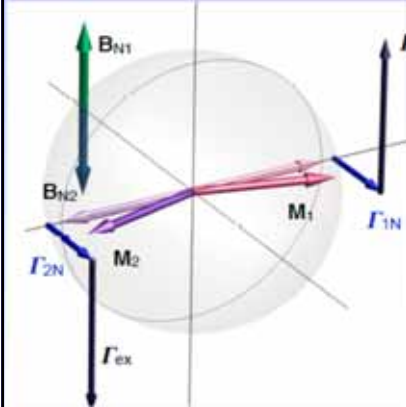
S. Bodnar, M. Jourdan, H. Gomonay, J. Sinova, T. Jungwirth, MK et al., Nature Comms. 9, 348 (2018);

3. Bulk spin orbit torque switching in Mn_2Au 

- Bi-polar switching using currents in perpendicular directions.
- Sign change of the PHE demonstrates switching of large part of domains.
- Very large PHE/AMR $>6\%$ can be reproduced by transport calculations.

S. Bodnar, M. Jourdan, H. Gomonay, J. Sinova, T. Jungwirth, MK et al., Nature Comms. 9, 348 (2018);

3. Combining reading and writing: interfacial SOT switching of NiO

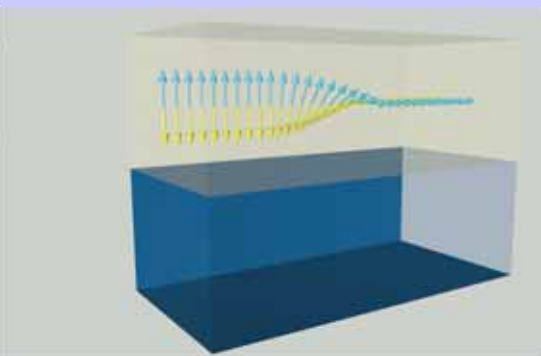
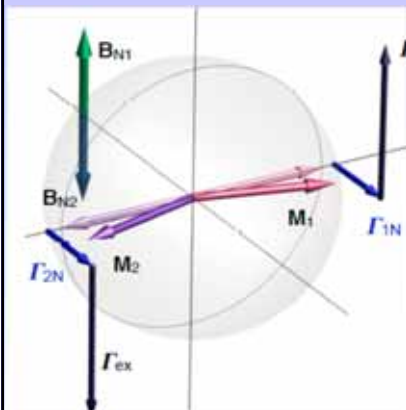


H. Gomonay, J. Sinova et al.,
Phys. Rev. Lett. **117**, 017202 ('16)

- Different switching mechanisms:
Domain Wall motion¹

¹T. Shiino et al., Phys. Rev. Lett. **117**, 087203 (2016); ²L. Baldrati, MK et al., arxiv:1810.11326 (PRL in press)

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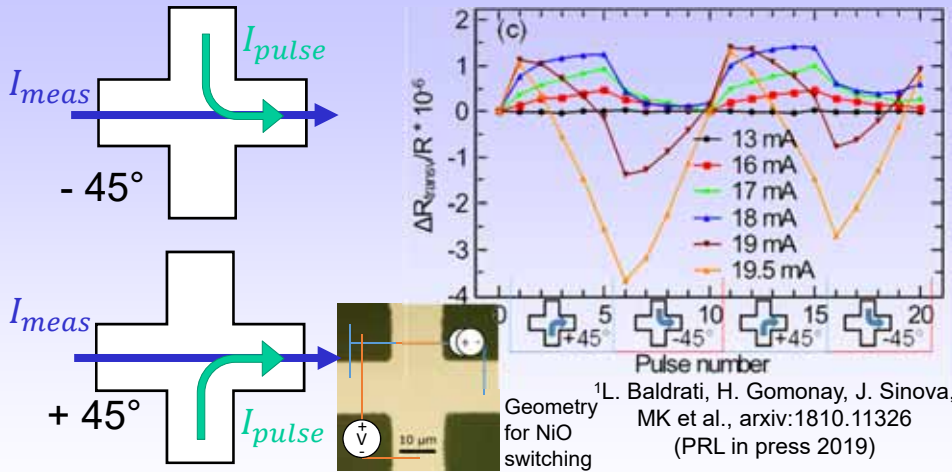


H. Gomonay, J. Sinova et al.,
Phys. Rev. Lett. **117**, 017202 ('16)

- Different switching mechanisms:
Domain Wall motion¹
Ponderomotive force²

¹T. Shiino et al., Phys. Rev. Lett. **117**, 087203 (2016); ²L. Baldrati, MK et al., arxiv:1810.11326 (PRL in press)

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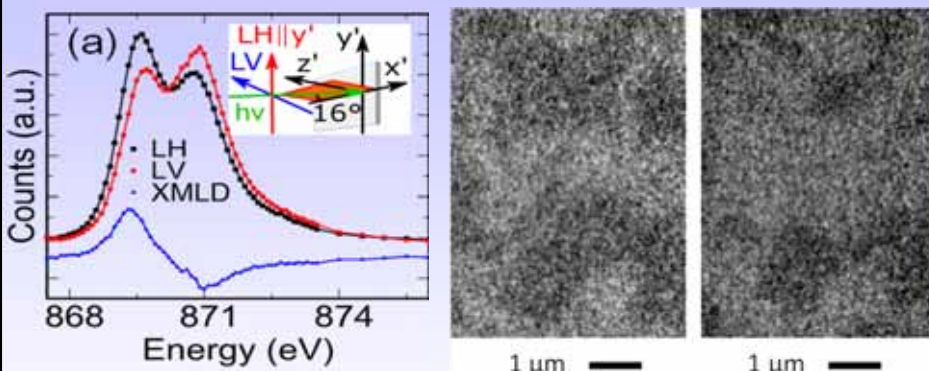


¹L. Baldrati, H. Gomonay, J. Sinova, MK et al., arxiv:1810.11326 (PRL in press 2019)
Geometry for NiO switching

- In combination with Pt layer, damping-like non-staggered SOTs generate 90° switching in NiO: Néel vector is rotated **parallel** to electron flow!¹
→ 2 effects: Néel vector change + structural changes in Pt layer?

See also Y. Cheng et al., arxiv:1906.04694 (2019); X. Chen et al., Phys. Rev. Lett. **120**, 207204 (2018)

3. Combining reading and writing: interfacial SOT switching of NiO



L. Baldrati, MK et al. arxiv:1810.11326 (2018), PRL in press

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→ 2 effects: Néel vector change + structural changes in Pt layer?

See also Y. Cheng et al., arxiv:1906.04694 (2019); X. Chen et al., Phys. Rev. Lett. **120**, 207204 (2018)

3. Summary of Writing:

- 1. Writing by magnetic fields:
Spin-flop
- 2. Writing by strain:
Magneto-elastic coupling
- 3. Writing by spin-orbit torques:
 - Bulk Néel staggered spin-orbit torques in metallic antiferromagnets with appropriate symmetry (Mn₂Au, CuMnAs)
 - Interfacial non-staggered spin-orbit torques in insulating AFM / Pt bilayer

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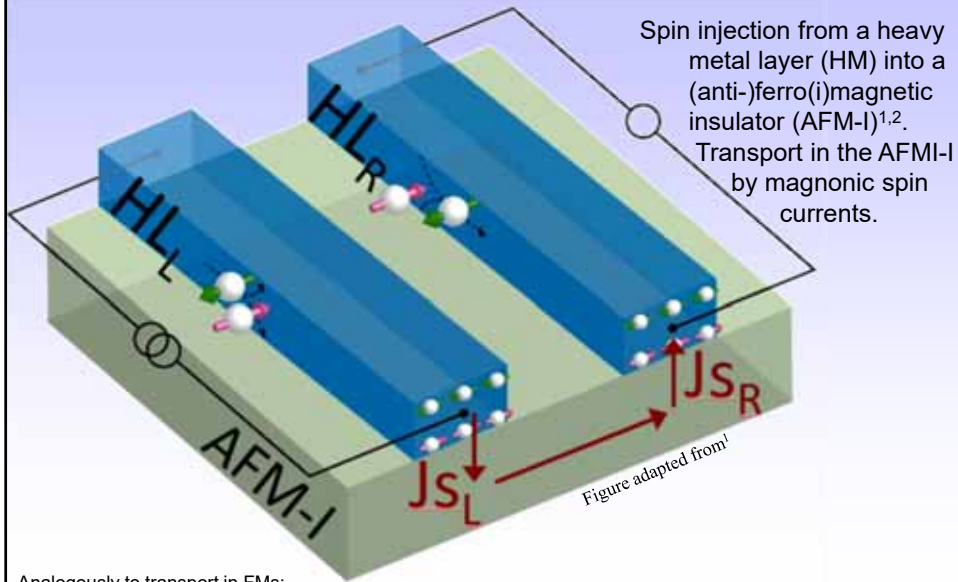
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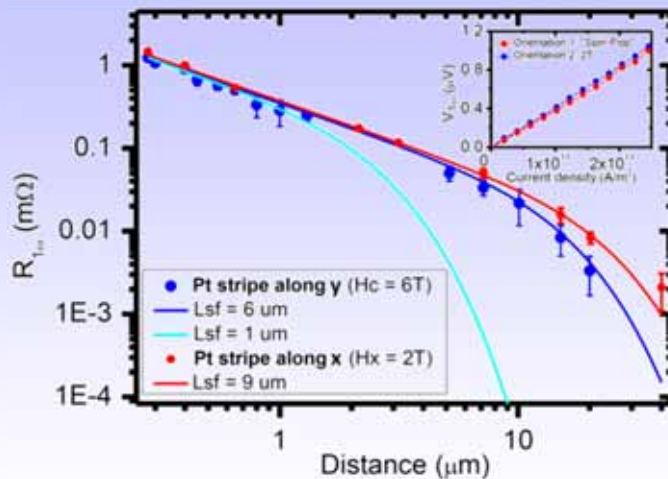
5. Lateral spin transport in antiferromagnetic insulators



Analogously to transport in FMs:

L. Cornelissen et al., Nature Phys. 11, 1022 (2015); K. Ganzhorn, MK et al., AIP Adv. 7, 085102 (2017)

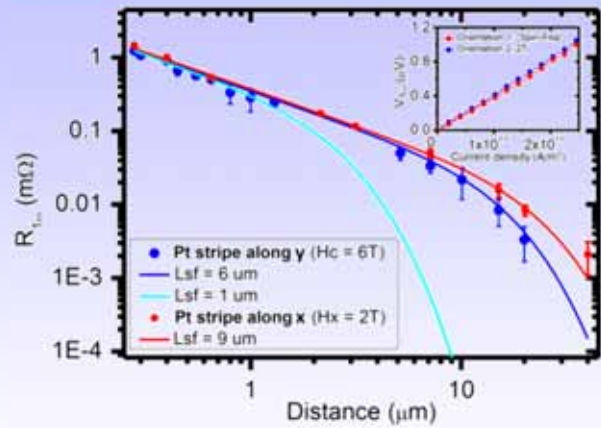
5. Quantifying spin transport & dissipation in bulk hematite



- Distance dependence: exponential decay \rightarrow diffusive spin transport
- Largest ever reported spin diffusion lengths for a magnetic insulator: 5-10 μm depending on applied field and transport over 40 μm observed!

R. Lebrun, A. Ross, S. Bender, A. Qaiumzadeh, A. Brataas, R. A. Duine, M. Kläui et al., Nature 561, 222 (2018)

5. Quantifying spin transport & dissipation in bulk hematite

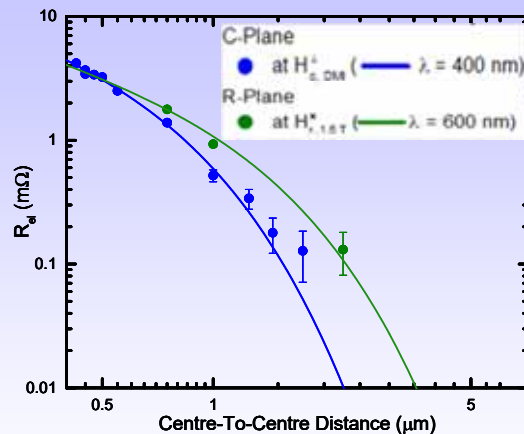


- No threshold
- Visible at high temperature
- Exponential decay
→ Diffusive transport over tens of microns in easy axis AFM!¹
- Previous transport in insulator AFMs only over few nm!²

¹R. Lebrun, A. Ross, S. Bender, A. Brataas, R. A. Duine, and M. Kläui Nature **561**, 222 (2018)
²PRL **113**, 97202 (2014); Nat. Comm. **9**, 1089; PRB **98**, 014409

	Experiments	Spin superfluid	Diffusive transport
Threshold	No	X	✓
Temperature	200 K	X	✓
Decay	Exponential (visible for large D)	X	✓

5. Quantifying spin transport in thin film hematite

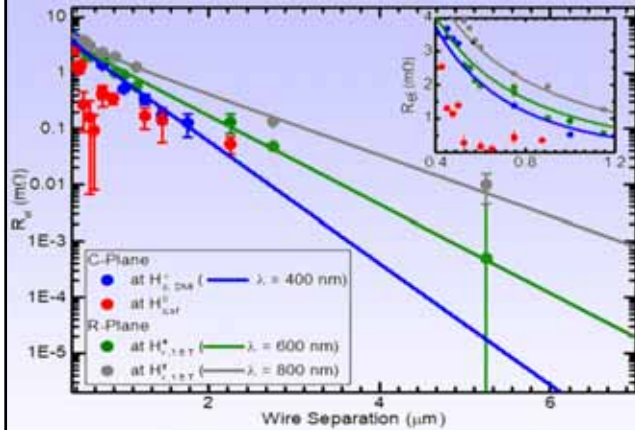


- μm diffusive transport in thin film antiferromagnet
- Origin of differences in spin diffusion lengths?:
 -Bulk Fe₂O₃: 5-10 μm¹
 -Thin film Fe₂O₃:
 c-cut: 400 nm
 r-cut: 600 nm
 -Thin film NiO: few nm²

¹R. Lebrun, A. Ross, S. Bender, A. Brataas, R. A. Duine, and M. Kläui Nature **561**, 222 (2018)
²PRL **113**, 97202 (2014); Nat. Comm. **9**, 1089; PRB **98**, 014409

	Experiments	Spin superfluid	Diffusive transport
Threshold	No	X	✓
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5. Quantifying spin transport in thin film hematite



- μm diffusive transport in thin film antiferromagnet
- Origin of differences in spin diffusion lengths?:
 - Bulk Fe_2O_3 : $5\text{-}10 \mu\text{m}^1$
 - Thin film Fe_2O_3 :
 - c-cut: 400 nm
 - r-cut: 600 nm
 - Thin film NiO : few nm^2
- Signal at spin-flop not simple diffusion \rightarrow reason?

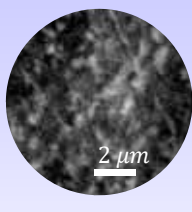
¹R. Lebrun, A. Ross, S. Bender, A. Brataas, R. A. Duine, and M. Kläui
Nature **561**, 222 (2018)

²PRL **113**, 97202 (2014); Nat. Comm. **9**, 1089; PRB **98**, 014409

	Experiments	Spin superfluid	Diffusive transport
Threshold	No	X	✓
Temperature	200 K	X	✓
Decay	Exponential (visible for large D)	X	✓

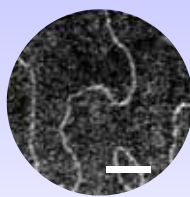
5. Correlating domain structures and spin transport lengths

C-Plane (0001) thin film¹
 $T > T_M$ (~easy-plane)



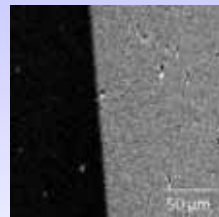
Domain size:
100 nm
 $\lambda < 100 \text{ nm}$

R-Plane (1102)¹
(thin film)



Domain size:
500 nm
 $\lambda = 600 \text{ nm}$

R-Plane (1102)²
(bulk)



Domain size:
> 10 μm
 $\lambda = 5\text{-}10 \mu\text{m}$

NiO (001) thin film³



Domain size:
< 100 nm
 $\lambda = \text{few nm}^2$

- Spin transport length scales with domain size.
- Circularly polarized magnons are predicted to be scattered from domain walls \rightarrow many domain walls \rightarrow scattering – magnon domain wall resistance!⁴
- Domain size can govern spin transport length due to DWs!¹

¹A. Ross, MK et al., arxiv:1907.02751; ²R. Lebrun, MK et al., Nature **561**, 222 (2018)

³L. Baldrati et al., Phys. Rev. B **98**, 024422 (2018); ⁴E. Tveten et al., Phys. Rev. Lett. **112**, 147204 (2014)

1. Great people@JGU

L. Baldrati, R. Lebrun, A. Ross, K. Lee,
C. Schmitt, N. Kerber, D. Han, R. Reeve
G. Karnad, S. Bodnar, A. Lucia, J. Kim,
M. Filianina, B. Seng, R. Reeve, J. Cram
D. Heinze, J. Zazvorka, R. Wu,



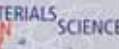
L. Baldrati, M. Weides, **H. Zabel, M. Jourdan, G. Jakob...and many former group members!**

2. Great collaborations:

O. Tretiakov, R. Ramos, E. Saitoh, G. Bauer, Tohoku; J. Barker, Leeds;
O. Gomonay, K. Everschor-Sitte, J. Sinova, J. Demsar, H. Elmers JGU
H. Stoll, M. Weigand, MPI-IS&BESSY; S. Finizio, J. Raabe PSI
F. Kronast, BESSY; F. Maccherozzi, DIAMOND; U. Nowak Konstanz
A. Brataas, A. Qaiumzadeh NTNU; S. Bender, R. Duine, Utrecht
T. Seifert, T. Kampfrath, FHI-MPG

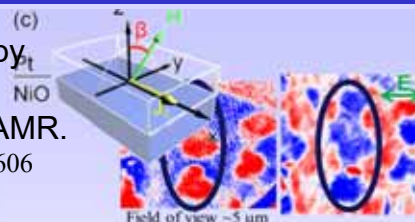
3. Funding

DFG (SPP SpinCaT, SFB TRR173, SPP Graphen, MAINZ), DAAD
EU (ITN MagnEFI, STREPs InSpin, A-SPIN, Nebula), CINEMA,
European Research Council Grants MASPIC & MultiRev, TopDyn
ICC-IMR Visiting Professor, Stanford-Tohoku-Mainz SpinNet, QuSpin

**Summary:**

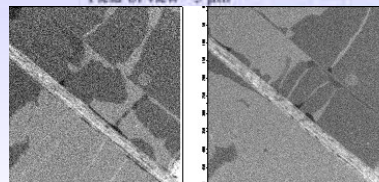
- Reading AFMs by XMLD-microscopy, and in insulators by spin Hall magnetoresistance and metals by AMR.

Phys. Rev. B. **98**, 024422 (2018); arxiv:1909.12606



- Writing AFM insulators and metals by Spin-Orbit torques due to DW motion & ponderomotive force effects

Nature Commun. **9**, 348 (2018); APL **109**, 142404 (2016); arxiv:1810.11326 (PRL in press 2019)



- Spin Transport in AFM insulators:
 - Observation of long-distance diffusive transport
 - Strong dependence on domain structure
 - spin transport can be tuned!

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